

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: $I_{F(AV)} \le 10 \text{ A}$
- Reverse voltage: $V_R \le 45 V$
- Low forward voltage
- High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; T _{sp} ≤ 130 °C; square wave	-	-	10	A
V _R	reverse voltage	T _j = 25 °C	-	-	45	V
V _F	forward voltage	I _F = 10 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	473	540	mV
I _R	reverse current	V_R = 10 V; $t_p \le 3$ ms; δ = 0.3; T_j = 25 °C; pulsed	-	13	30	μA
		V_R = 45 V; $t_p \le 3$ ms; δ = 0.3; T _j = 25 °C; pulsed	-	150	500	μA





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		
2	А	anode		
3	к	cathode	(2) CFP15 (SOT1289)	

6. Ordering information

Fable 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMEG45A10EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: $5.8 \times 4.3 \times 0.78 \text{ mm}$	SOT1289				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG45A10EPD	4510 AAAA

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	45	V
I _F	forward current	T _{sp} = 125 °C; δ = 1		-	14	А
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; T _{sp} ≤ 130 °C; square wave		-	10	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	170	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.9	W
			[2]	-	1.2	W
			[3]	-	3	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C

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Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

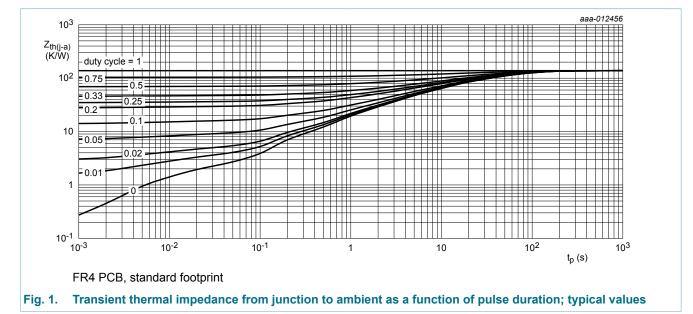
[3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	-	165	K/W	
			[1][3]	-	-	120	K/W	
			[1][4]	-	-	50	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	4	K/W	

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

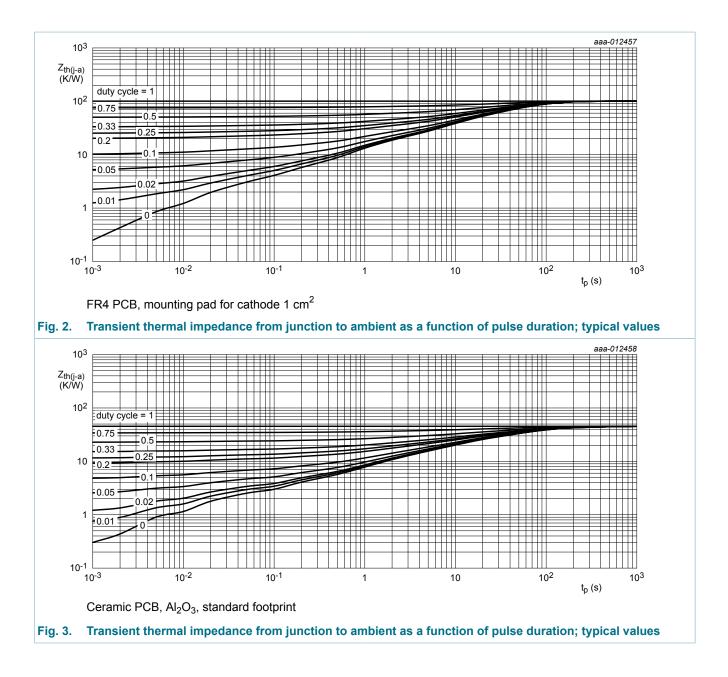
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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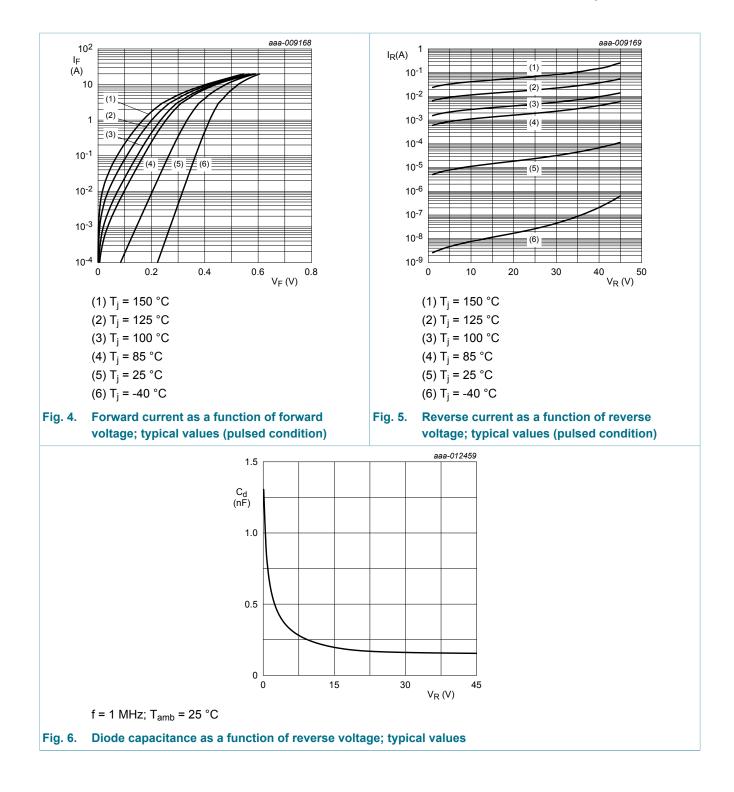
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I_F = 1 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	330	380	mV
		I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	357	-	mV
		$I_{F} = 3 \text{ A}; t_{p} \le 300 \mu\text{s}; \delta \le 0.02;$ $T_{j} = 25 \text{ °C}; \text{ pulsed}$	-	377	-	mV
		I_F = 5 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	409	470	mV
		I _F = 10 A; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C; pulsed	-	473	540	mV
I _R	reverse current	V_{R} = 5 V; t_{p} ≤ 3 ms; δ = 0.3; T_{j} = 25 °C; pulsed	-	10	-	μA
		V_R = 10 V; $t_p \le 3$ ms; δ = 0.3; T_j = 25 °C; pulsed	-	13	30	μA
		V_R = 30 V; $t_p \le$ 3 ms; δ = 0.3; T_j = 25 °C; pulsed	-	36	-	μA
		V_R = 45 V; $t_p \le 3$ ms; δ = 0.3; T_j = 25 °C; pulsed	-	150	500	μA
		V_R = 10 V; $t_p \le 3$ ms; δ = 0.3; T_j = 125 °C; pulsed	-	11	-	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	715	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	240	-	pF
t _{rr}	reverse recovery time ; step recovery	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	21	-	ns
t _{rr}	reverse recovery time ; ramp recovery	dI _F /dt = 200 A/µs; T _j = 25 °C; I _F = 6 A; V _R = 26 V	-	13	-	ns
V _{(BR)R}	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; $t_p \le$ 1.2 ms; δ = 0.12; pulsed	45	-	-	V
V _{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C}$	-	317	-	mV

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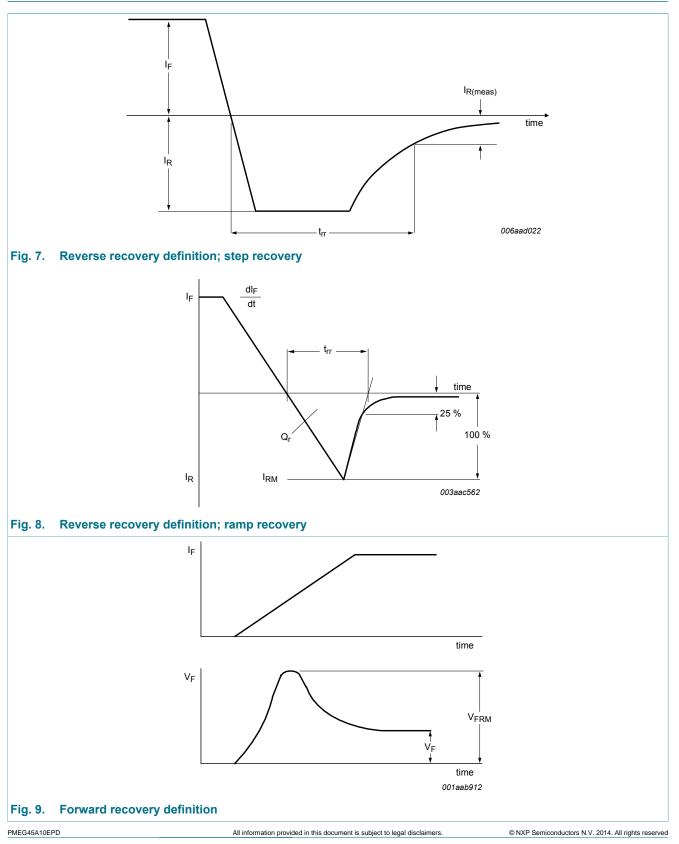


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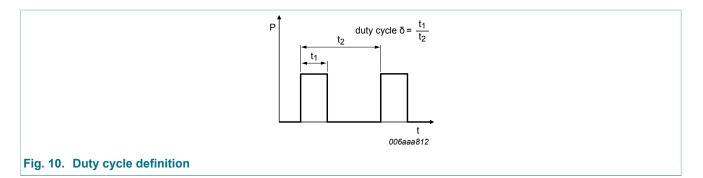
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11. Test information



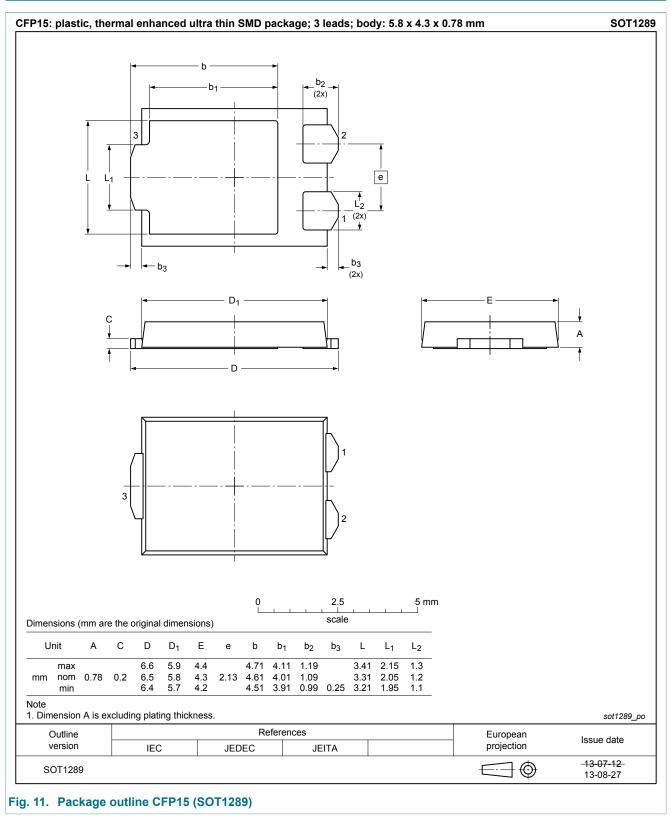
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The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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12. Package outline

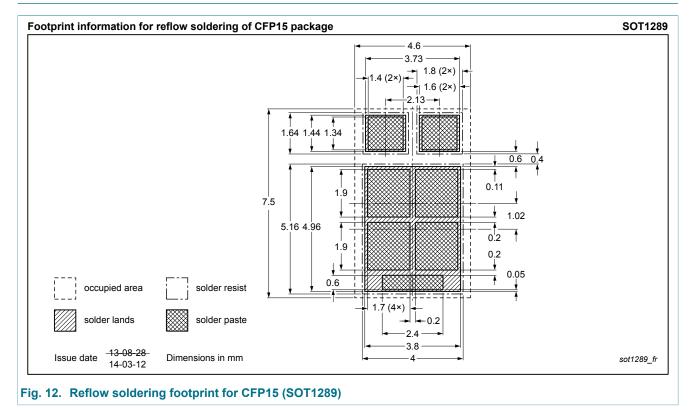


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13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG45A10EPD v.2	20140416	Product data sheet	-	PMEG45A10EPD v.1			
Modifications:	Product status char	iged	·				
PMEG45A10EPD v.1	20140217	Objective data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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